

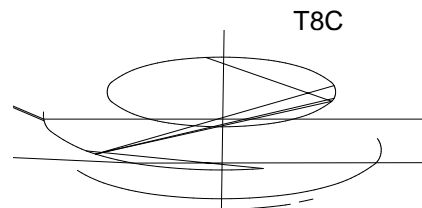
KK1100-FAST SWITCHING THYRISTOR

2500-2800 V_{DRM}

HIGH POWER THYRISTOR FOR INVERTER APPLICATION

Features:

- . All Diffused Structure
- . Amplifying Gate Configuration
- . Blocking capability up to 2800 volts
- . High dv/dt Capability
- . Pressure Assembled Device



ELECTRICAL CHARACTERISTICS AND RATINGS

Blocking - Off State

Device Type	V _{RRM} (1)	V _{DRM} (1)	V _{RSM} (1)
KK1100/25	2500	2500	2700
KK1100/28	2800	2800	3000

V_{RRM} = Repetitive peak reverse voltage

V_{DRM} = Repetitive peak off state voltage

V_{RSM} = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage and off state leakage	I _{RRM} /I _{DRM}	5 mA 100 mA (3)
Critical rate of voltage rise	dv/dt (4)	1000 V/μs

Conducting - On State

ELECTRICAL CHARACTERISTICS AND RATINGS KK1100-FAST SWITCHING THYRISTOR

Gating

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Peak gate power dissipation						

